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What is claimed is:

- 1. A heterojunction structure comprising a p-type semiconductor thin film and an n-type ZnO-based nanorod epitaxially grown thereon.
- 2. The heterojunction structure of claim 1, wherein the p-type semiconductor is made of a material having a band-gap energy ranging from 1.5 to 4.5 eV.
- 3. The heterojunction structure of claim 2, wherein p-type semiconductor is made of a material selected from the group consisting of GaN, AlN, GaP, GaAs, ZnSe, CdSe, CdS, ZnS, SrCu₂O₂, SiC and Si.
- 4. The heterojunction structure of claim 1, wherein the p-type semiconductor thin film has a thickness ranging from 50 nm to 200 μ m.
 - 5. The heterojunction structure of claim 1, wherein the ZnO-based nanorod has a diameter in the range of 5 to 100 nm and a length in the range of 5 nm to 100 μ m.

6. The heterojunction structure of claim 1, wherein the ZnO-based nanorod is a ZnO nanorod or a heteromaterial-doped or coated ZnO-nanorod.

- 7. The heterojunction structure of claim 6, wherein the heteromaterial is selected from the group consisting of Mg, Mn, Cd, Se and mixtures thereof.
 - 8. The heterojunction structure of claim 6, wherein the doped

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heteromaterial is selected from the group consisting of $Zn_{1-x}Mg_xO$ (0<x<1), $Zn_{1-x}Mn_xO$ (0<x<1), $Zn_{1-x}Cd_xO$ (0<x<1) and $Zn_{1-x}Se_xO$ (0<x<1).

- 9. A method for preparing the heterojunction structure of claim 1, which comprises bringing the vapors of a Zn-containing metal organic compound and an O_2 -containing compound as reactants separately into contact with a ptype semiconductor thin film at a temperature in the range of 400 to 700 $^{\circ}$ C under a pressure in the range of 0.1 to 10 torr to form a ZnO nanorod on the surface of the semiconductor film.
- 10. A nano-device or an array thereof comprising the heterojunction structure of claim 1.
- 11. A nano-system or an integrated circuit comprising the nano-device array of claim 10.